

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
20V	20mΩ@4.5V	5A
	26mΩ@2.5V	



合肥矽普半导体

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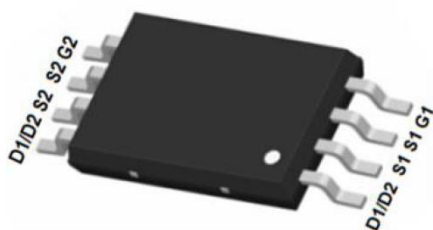
Feature

- High power and current handling capability
- Surface mount package

Application

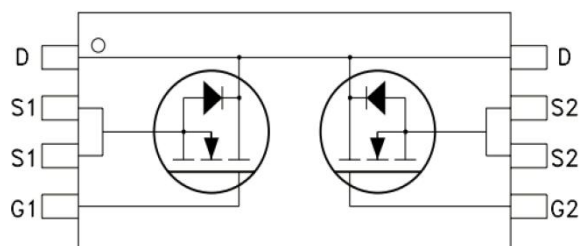
- Battery Switch
- DC/DC Converter

Package

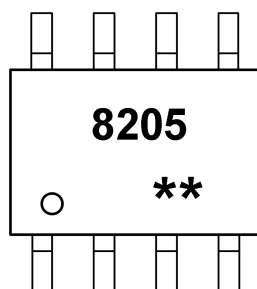


TSSOP-8L

Circuit diagram



Marking



8205
**

:Device Code
:Week Code

Order Information

Device	Package	Unit/Tape
SP8205DS8	TSSOP-8L	4000

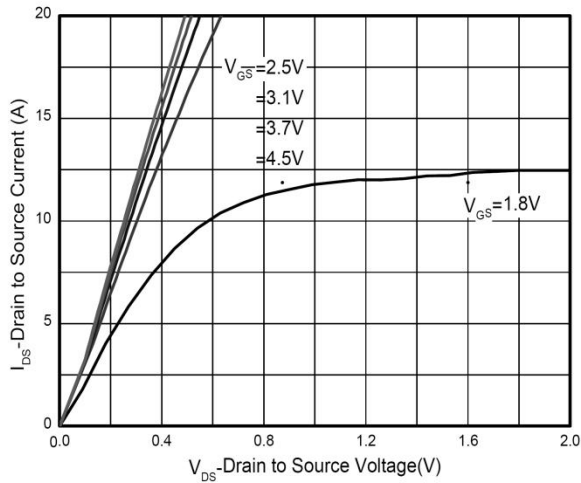
Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	5	A
Pulse Drain Current Tested	I_{DM}	20	A
Power Dissipation	P_D	1.5	W
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	83.3	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

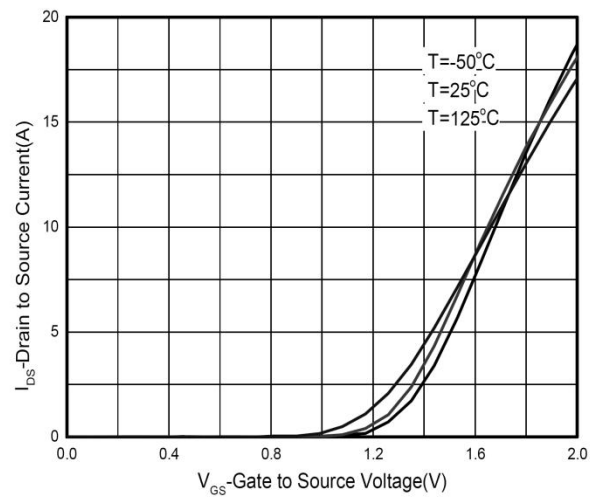
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250μA	20	-	-	V
Drain-Source Leakage Current	IDSS	VDS=16V , VGS=0V	-	-	1	uA
Gate-Source Leakage Current	IGSS	VGS=±12V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VDS=VGS , ID=250μA	0.5	0.66	1.2	V
Static Drain-Source On-Resistance	RDS(ON)	VGS=4.5V , ID =4.5A	-	20	27	mΩ
		VGS=2.5V , ID =3.5A	-	26	32	
Dynamic characteristics						
Input Capacitance	Ciss	VDS=10V , VGS=0V , f=1MHz	-	415	-	pF
Output Capacitance	Coss		-	87	-	
Reverse Transfer Capacitance	Crss		-	70	-	
Total Gate Charge	Qg	VDS=10V , VGS=4.5V , ID=4A	-	6.5	-	nC
Gate-Source Charge	Qgs		-	1.2	-	
Gate-Drain Charge	Qgd		-	1.5	-	
Switching Characteristics						
Turn-On Delay Time	td(on)	VDD=10V , VGS=4.5V , RG=3Ω , ID=1A	-	4.5	-	nS
Turn-On Rise Time	tr		-	80	-	
Turn-Off Delay Time	td(off)		-	25	-	
Turn-Off Fall Time	tf		-	23	-	
Source-Drain Diode characteristics						
Diode Forward Voltage	VSD	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V

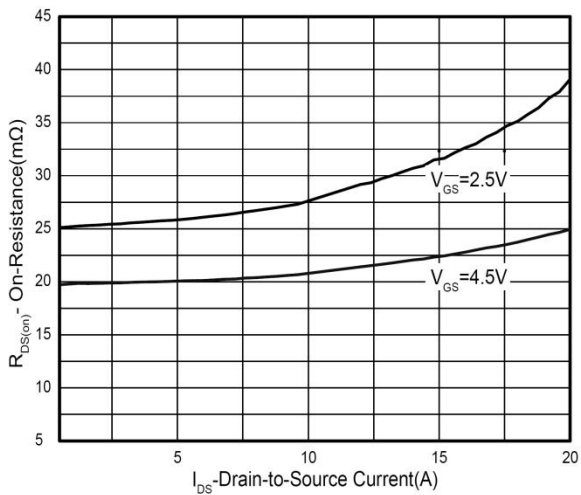
Typical Characteristics



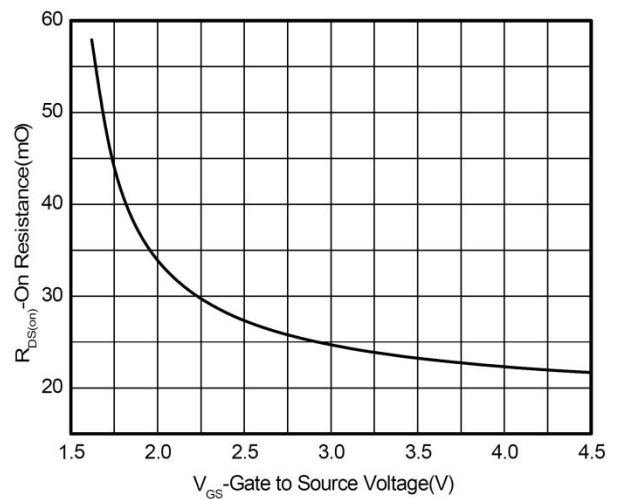
Output characteristics



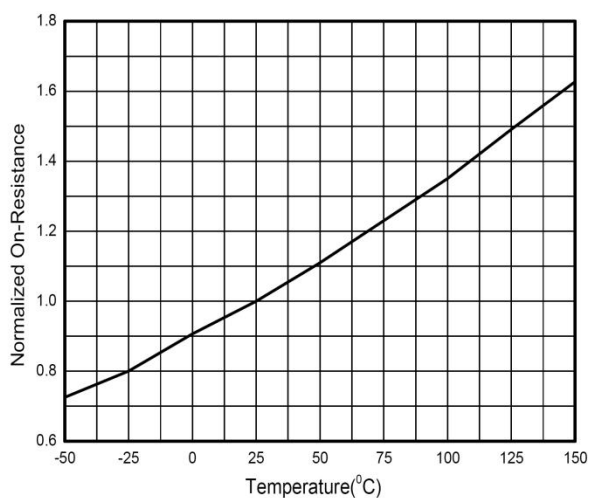
Transfer characteristics



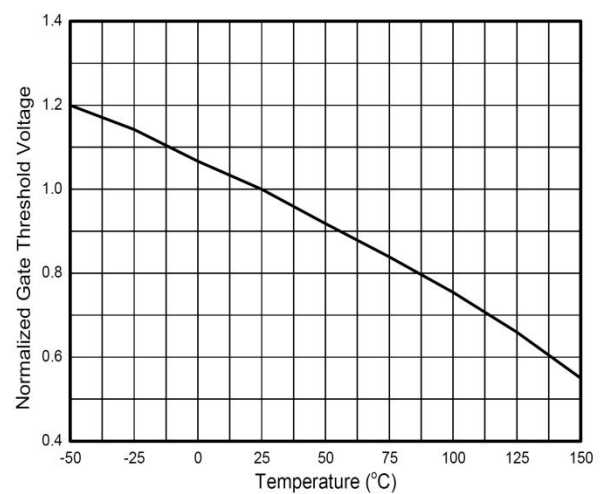
On-Resistance vs. Drain current



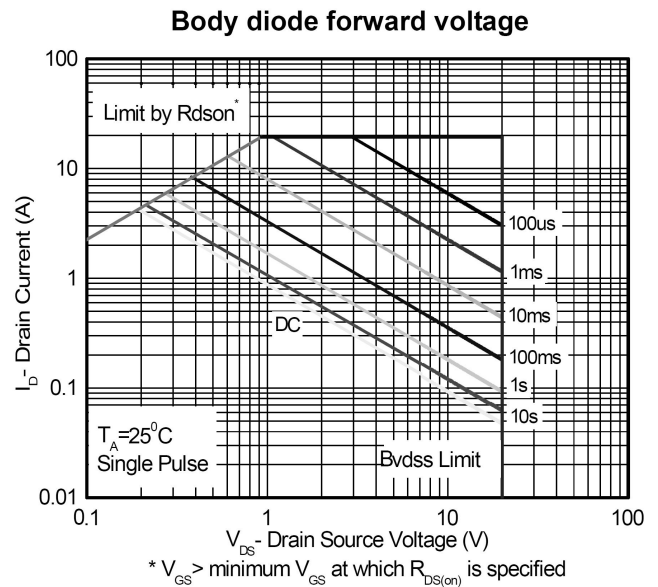
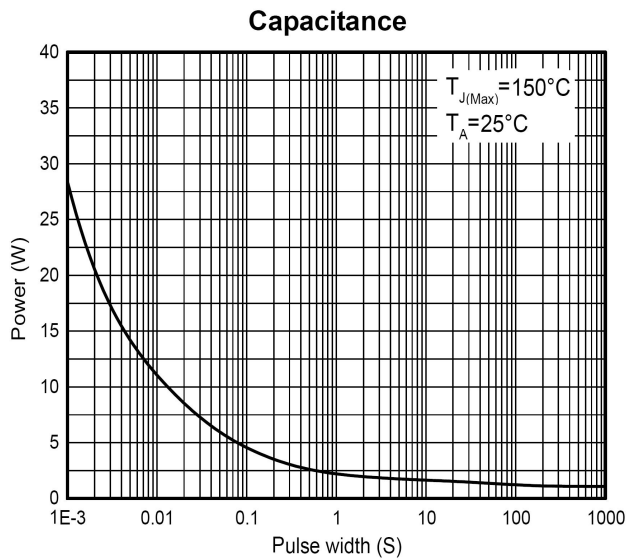
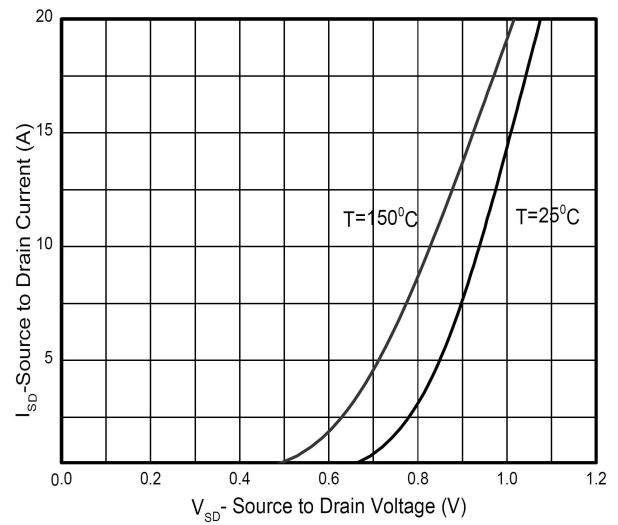
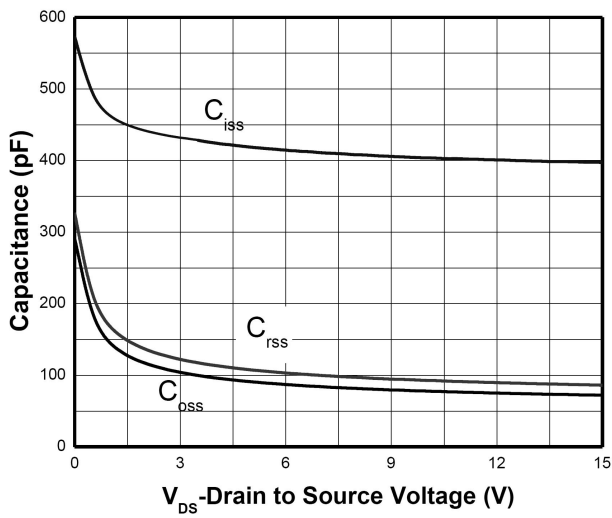
On-Resistance vs. Gate-to-Source voltage



On-Resistance vs. Junction temperature

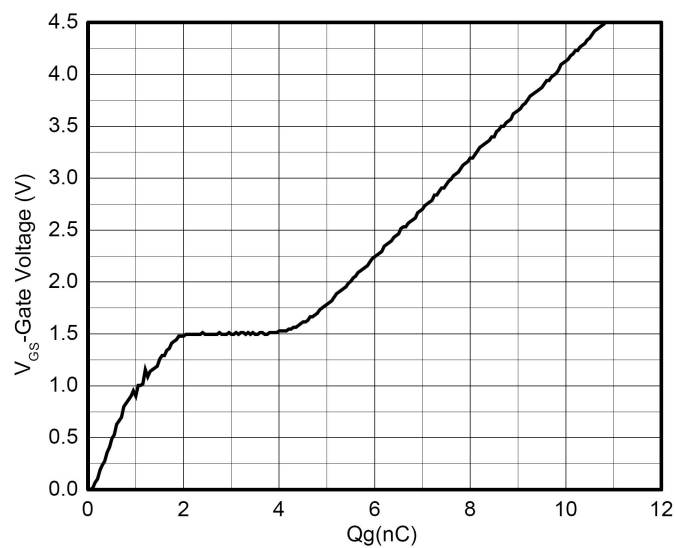


Threshold voltage vs. Temperature



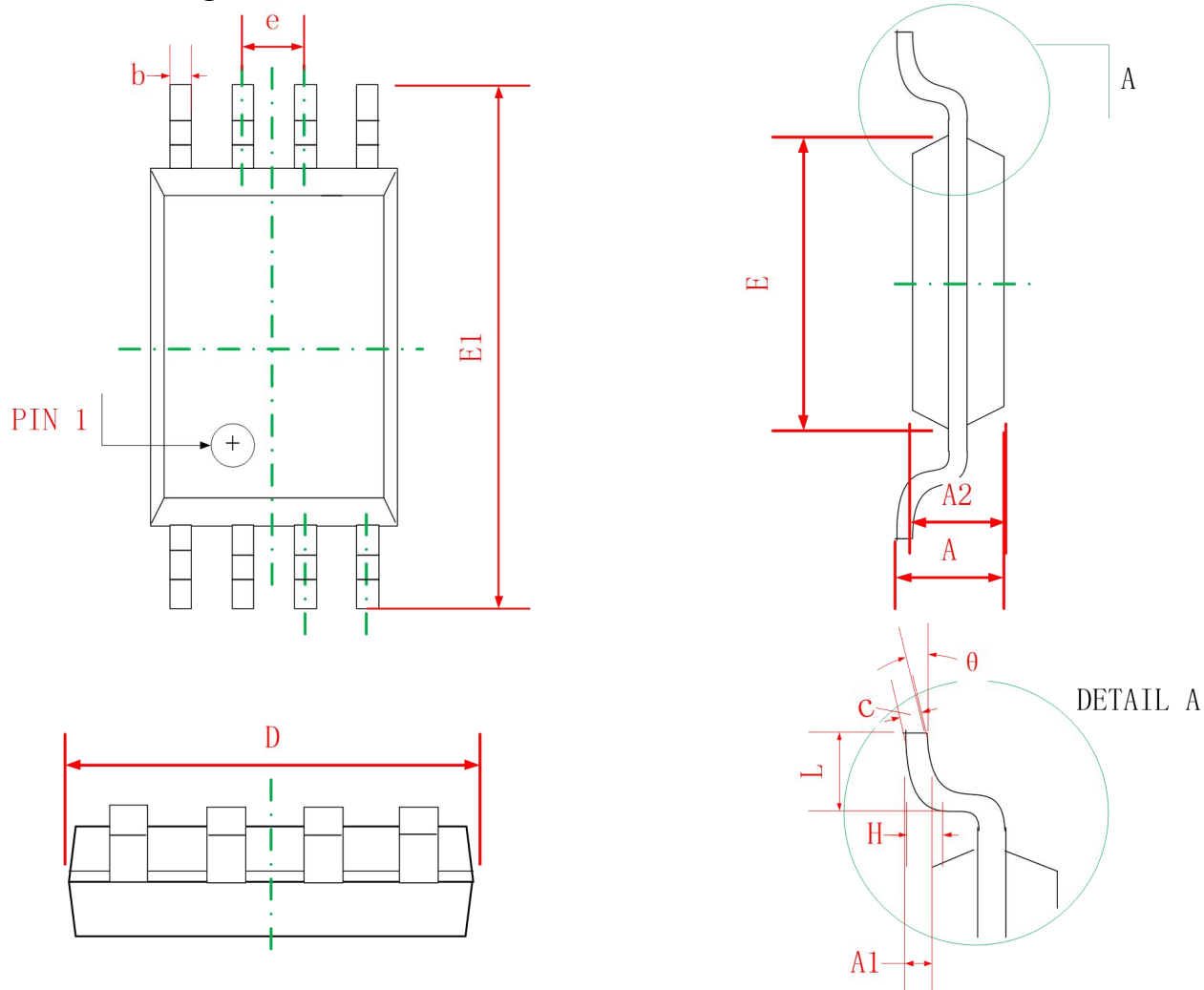
Single pulse power

Safe operating power



Gate charge Characteristics

TSSOP-8L Package Information



Symbol	Dimensions In Millimeters	
	Min	Max
D	2.900	3.100
E	4.300	4.500
b	0.190	0.300
c	0.090	0.200
E1	6.250	6.550
A		1.200
A2	0.800	1.000
A1	0.050	0.150
e	0.65(BSC)	
L	0.500	0.700
H	0.25(TYP)	
θ	1°	7°